

FDC642P

P-Channel 2.5V Specified PowerTrench™ MOSFET

General Description

This P-Channel 2.5V specified MOSFET is produced using Fairchild's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

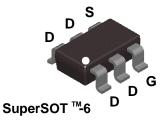
These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the larger packages are impractical.

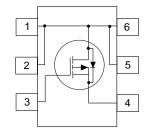
Applications

- Load switch
- · Battery protection
- · Power management

Features

- -4 A, -20 V. $R_{DS(ON)} = 0.065 \Omega$ @ $V_{GS} = -4.5 V$ $R_{DS(ON)} = 0.100 \Omega$ @ $V_{GS} = -2.5 V$
- · Fast switching speed.
- · Low gate charge (7.2nC typical).
- High performance trench technology for extremely low $R_{\scriptscriptstyle DS(\text{ON})}.$
- SuperSOT[™]-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{DSS}	Drain-Source Voltage	-20	V	
V _{GSS}	Gate-Source Voltage	±8	V	
I _D	Drain Current - Continuous	(Note 1)	-4	Α
	Drain Current - Pulsed	(Note 1a)	-20	
P _D	Power Dissipation for Single Operation	(Note 1a)	1.6	W
		(Note 1b)	0.8	1
T _J , T _{stg}	Operating and Storage Junction Temperature	-55 to +150	°C	

Thermal Characteristics

R _e JA	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R _a JC	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity	
.642	FDC642P	7"	8mm	3000 units	

Symbol	Parameter	Min	Тур	Max	Units	
Off Char	acteristics	1	I		I.	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-16		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 8 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -8 V, V _{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-0.4	-0.7	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		2.5		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -4 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -4 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = -2.5 \text{ V}, I_D = -3.2 \text{ A}$		0.054 0.076 0.077	0.065 0.105 0.100	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = -4.5 V, V _{DS} = -5 V	-10			Α
g FS	Forward Transconductance	V _{DS} = -5 V, I _D = -4 A		9		S
Dvnamic	Characteristics					
Ciss	Input Capacitance	V _{DS} = -10 V, V _{GS} = 0 V		640		pF
Coss	Output Capacitance	f = 1.0 MHz		180		pF
C _{rss}	Reverse Transfer Capacitance			90		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	V _{DD} = -10 V, I _D = -1 A		11	20	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		19	30	ns
t _{d(off)}	Turn-Off Delay Time			26	42	ns
t _f	Turn-Off Fall Time			35	55	ns
Qg	Total Gate Charge	V _{DS} = -10 V, I _D = -4 A		7.2	10	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 V,$		1.7		nC
Q _{gd}	Gate-Drain Charge			1.6		nC
Drain-Sc	ource Diode Characteristics and	d Maximum Ratings				
Is	Maximum Continuous Drain-Source Did				-1.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -1.3 A (Note 2)		-0.75	-1.2	V

Notes

a) 78° C/W when mounted on a 1.0 in² pad of 2 oz. copper.

b) 156° C/W when mounted on a minimum pad of 2 oz.copper.

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

^{1.} $R_{B,IA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{B,IC}$ is guaranteed by design while $R_{B,CA}$ is determined by the user's board design.

Typical Characteristics

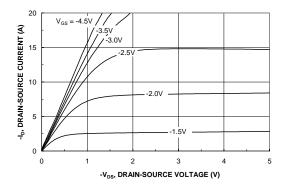


Figure 1. On-Region Characteristics.

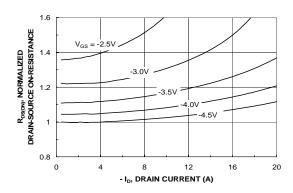


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

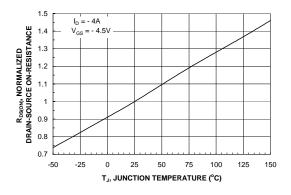


Figure 3. On-Resistance Variation with Temperature.

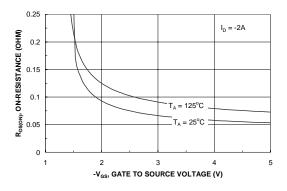


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

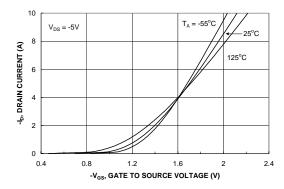


Figure 5. Transfer Characteristics.

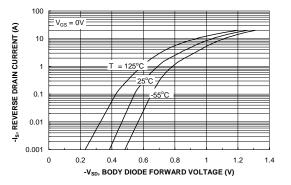
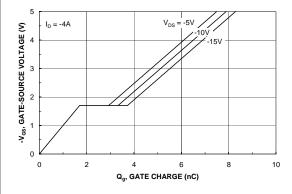


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



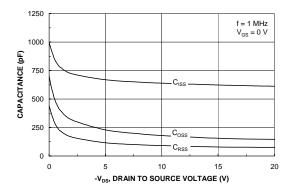
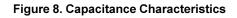
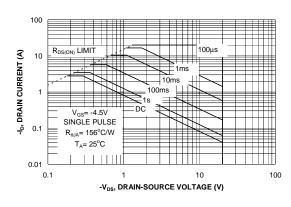


Figure 7. Gate-Charge Characteristics





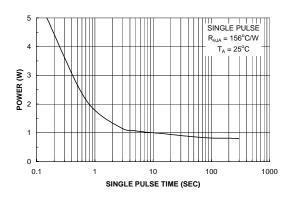


Figure 9. Maximum Safe Operating Area

Figure 10. Single Pulse Maximum Power Dissipation

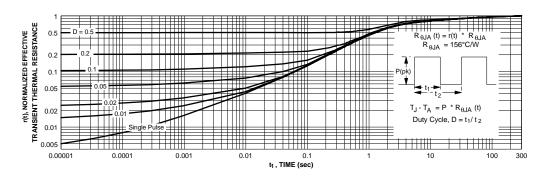
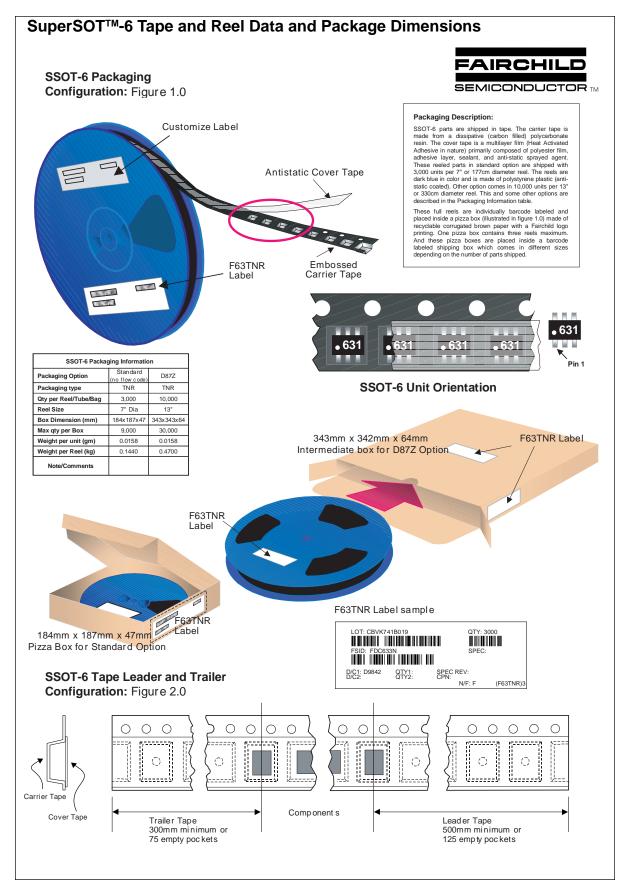
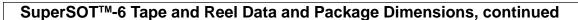


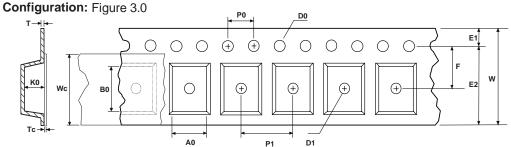
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient themal response will change depending on the circuit board design.





SSOT-6 Embossed Carrier Tape



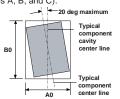


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

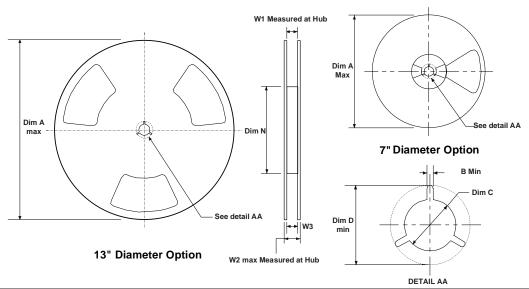


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

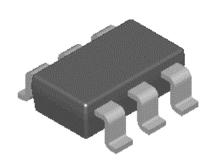
SSOT-6 Reel Configuration: Figure 4.0

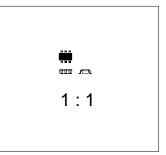


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT[™]-6 Tape and Reel Data and Package Dimensions, continued

SuperSOT™-6 (FS PKG Code 31, 33)

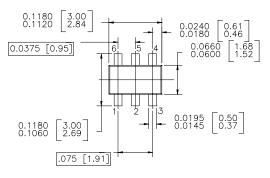


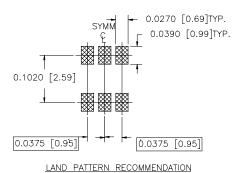


Scale 1:1 on letter size paper

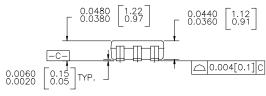
Dimensions shown below are in: inches [millimeters]

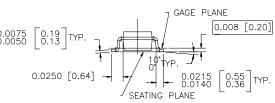
Part Weight per unit (gram): 0.0158





CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH: 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

SUPER SOT 6 LEADS

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FACTTM QSTM

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